

In the Specification:

Please amend the following paragraph previously added after paragraph [0023]:

An alternative embodiment of the invention is illustrated in Figure 4, which includes Figures 4A-~~[[4E]]~~ 4F. A pad oxide layer 301 is deposited atop the substrate 200, and a pad nitride layer 303 is deposited atop the pad oxide layer 301. A hard mask layer 202 is deposited atop the pad nitride layer 303, and a layer of resist 204 is deposited atop the hard mask layer 202 (Figure 4A). As illustrated now in Figure 4B, the layer of resist 204 is patterned to form a ring of resist 206 which separates a periphery of the substrate 200 from a further region of the substrate 200, thereby protecting devices formed in the further region of the substrate 200 from shining spots present in the periphery of the substrate 200. As illustrated in Figure 4C, a further layer of resist 208 is deposited atop the hard mask layer 202 and atop the ring of resist 206, and the further layer of resist 208 is patterned to form at least one patterned region 210 within the further region of the substrate 200 (Figure 4D). The ring of resist 206 is of sufficient thickness that a region of the further layer of resist 208 that is atop the ring of resist 206 is not patterned. The hard mask layer 202 is etched using the patterned further layer of resist 208 and the ring of resist 206 as an etch mask (Figure 4E). As illustrated in Figure ~~[[4E]]~~ 4F, at least one trench region 320 in the substrate 200 is etched using the hard mask layer 202 and the ring of resist 206 as an etch mask. The ring of resist 206 is of sufficient thickness such that a region of the hard mask layer 202 that is beneath the ring of resist 206 remains after the trench region 320 is etched.